

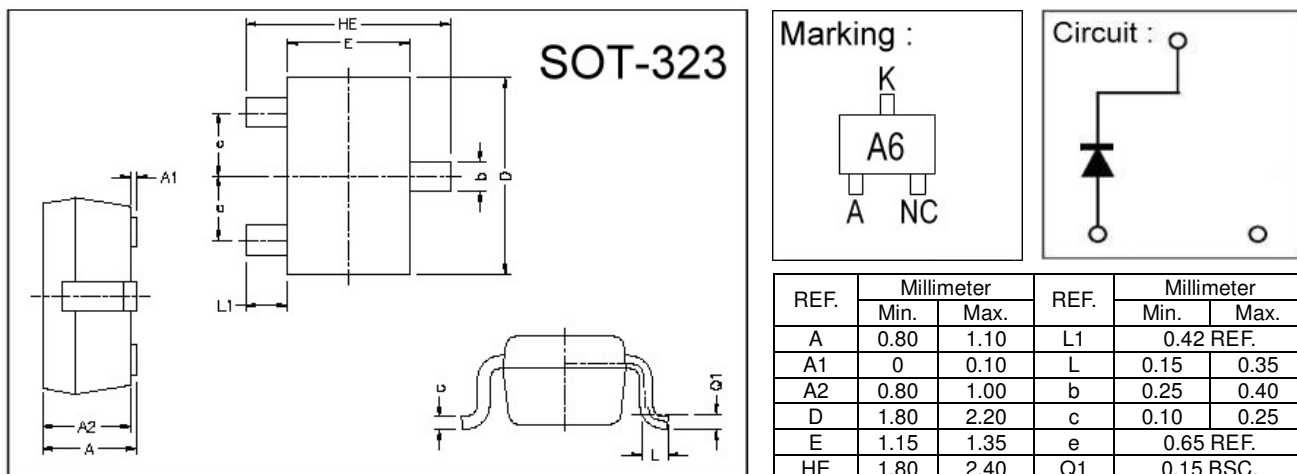
## GSBAS16

**SURFACE MOUNT, SWITCHING DIODE**  
**VOLTAGE 85V, CURRENT 250mA**

### Description

The GSBAS16 is designed for high-speed switching application in hybrid thick and thin-film circuits. The devices is manufactured by the silicon epitaxial planar process and packed in a plastic surface mount package.

### Package Dimensions



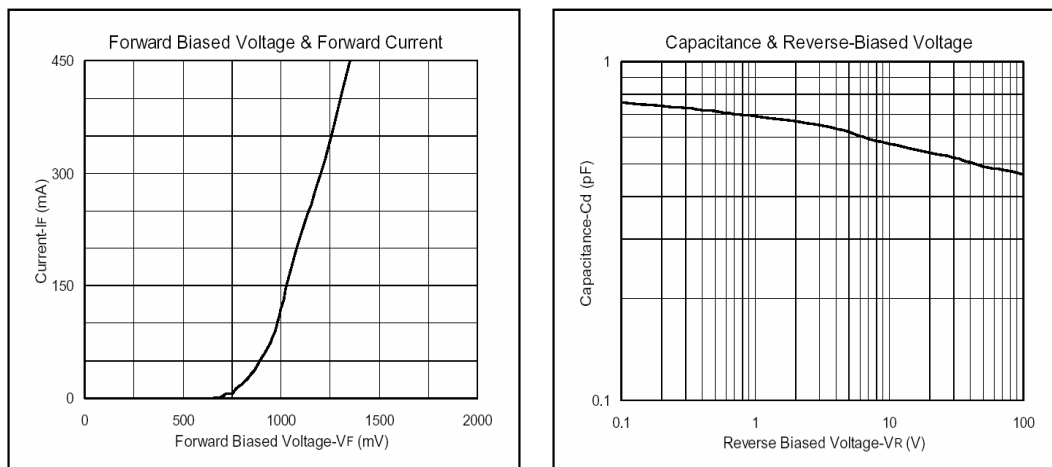
### Absolute Maximum Ratings at TA = 25°C

| Parameter                   | Symbol           | Ratings    | Unit |
|-----------------------------|------------------|------------|------|
| Junction Temperature        | T <sub>j</sub>   | +150       | °C   |
| Storage Temperature         | T <sub>stg</sub> | -65 ~ +150 | °C   |
| Reverse Voltage             | V <sub>R</sub>   | 85         | V    |
| Repetitive Reverse Voltage  | V <sub>RRM</sub> | 85         | V    |
| Forward Current             | I <sub>O</sub>   | 250        | mA   |
| Repetitive Forward Current  | I <sub>FM</sub>  | 500        | mA   |
| Forward Surge Current (1ms) | I <sub>FSM</sub> | 1000       | mA   |
| Total Power Dissipation     | P <sub>D</sub>   | 225        | mW   |

### Electrical Characteristics (at TA = 25°C unless otherwise noted)

| Characteristic            | Symbol             | Min. | Max. | Unit | Test Conditions                                                                            |
|---------------------------|--------------------|------|------|------|--------------------------------------------------------------------------------------------|
| Reverse Breakdown Voltage | V <sub>(BR)</sub>  | 85   | -    | V    | I <sub>R</sub> =100uA                                                                      |
| Forward Voltage           | V <sub>F</sub> (1) | -    | 715  | mV   | I <sub>F</sub> =1mA                                                                        |
|                           | V <sub>F</sub> (2) | -    | 855  | mV   | I <sub>F</sub> =10mA                                                                       |
|                           | V <sub>F</sub> (3) | -    | 1000 | mV   | I <sub>F</sub> =50mA                                                                       |
|                           | V <sub>F</sub> (4) | -    | 1250 | mV   | I <sub>F</sub> =150mA                                                                      |
| Reverse Current           | I <sub>R</sub>     | -    | 1    | uA   | V <sub>R</sub> =85V                                                                        |
| Total Capacitance         | C <sub>T</sub>     |      | 2    | pF   | V <sub>R</sub> =0, f=1MHz                                                                  |
| Reverse Recovery Time     | T <sub>rr</sub>    | -    | 6    | nS   | I <sub>F</sub> =I <sub>R</sub> =10mA, R <sub>L</sub> =100Ω measured at I <sub>R</sub> =1mA |

## Characteristics Curve

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